

# BSTMX42-0205 2-4.5 GHz I/Q Mixer Data Sheet

#### I. Product Introduction

BSTMX42-0205 is an I/Q mixer chip with RF and LO frequencies of 2 to 4.5 GHz, an IF frequency of DC to 1.5 GHz, and a conversion loss of 8.5 dB.

## **II. Application Areas**

- Radar
- Communications
- Instruments

## **III. Key Technical Indicators**

•	RF & LO frequency:	2~4.5GHz
•	IF frequency:	DC~1.5GHz
•	Local oscillator power:	16dBm
•	Conversion loss:	8.5dB
•	LO/RF isolation:	40dB
•	Image suppression:	30dBc
•	Input 1dB compression point:	14dBm
•	Chip size:	2.06mm x 1.66mm

## IV. Electrical properties (T<sub>A</sub>=25 °C)

Table 1

INDEX	MINIMUM	TYPICAL VALUES	MAXIMUM
RF & LO frequency (GHz)	2 ~ 4.5		
IF frequency (GHz)	DC ~ 1.5		
Conversion loss (dB)	_	8.5	_



INDEX	MINIMUM	TYPICAL VALUES	MAXIMUM
Image rejection (dBc)	_	30	_
LO~RF isolation (dB)	_	40	_
LO~IF isolation (dB)	_	25	_
RF~IF isolation (dB)	_	40	_
Input 1dB compression point (dBm)	_	14	_

## V. Absolute Maximum Ratings

Table 2

PARAMETER	LIMIT VALUE
Maximum input power	+20dBm
Operating temperature	-55 °C∼ +125 °C
Storage temperature	-65 °C∼ +150 °C

## VI. Typical test curves where $I_F$ = 0.5GHz unless otherwise specified

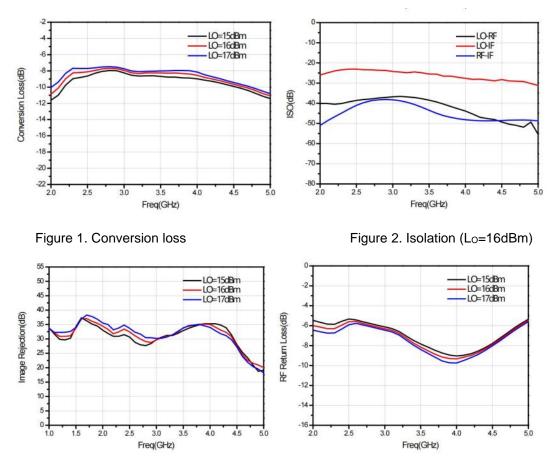


Figure 3. Image rejection

Figure 4. RF return loss



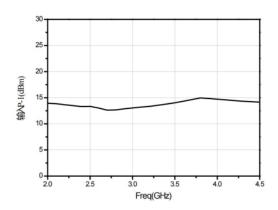


Figure 5. Input 1dB compression point

# VII. Overall and Port Dimensions (mm)

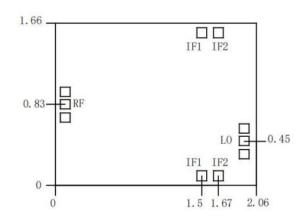


Figure 6

# VIII. Assembly package Diagram

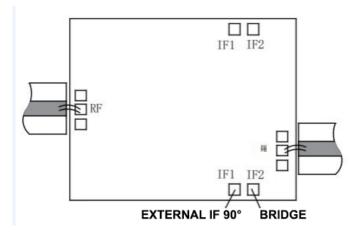


Figure 7



#### IX. Schematic

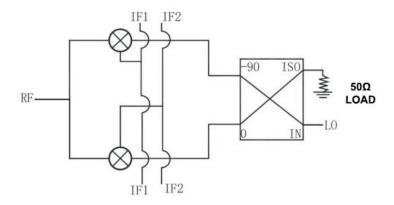


Figure 8.

#### X. Precautions

- The chip should be stored in a dry, nitrogen-filled environment and used in an ultraclean environment;
- GaAs material is brittle and the chip surface cannot be touched. Be careful when using it;
- Sinter the chip with conductive glue or alloy (the alloy temperature cannot exceed 300 °C and the time cannot exceed 30 seconds) to ensure that it is fully grounded;
- The gap between the chip microwave port and the substrate should not exceed 0.05mm. Use 25µm double gold wire bonding. The recommended gold wire length is 250 to 400µm;
- The chip has a DC-blocking capacitor on the RF side, but not on the LO and IF sides.
- The chip is sensitive to static electricity; please use anti-static measures during storage and use.